

## **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently amended) An etching method for etching an organic etching target film ~~formed on an SiO<sub>2</sub> film placed inside an airtight processing chamber~~, the method comprising:

forming the organic etching target film on a protective film placed inside an airtight processing chamber, the organic etching film containing Si;

introducing a processing gas into ~~[[said]]~~ the airtight processing chamber, ~~wherein said the processing gas contains~~ containing N<sub>2</sub> and at least one of C<sub>4</sub>F<sub>8</sub> and CF<sub>4</sub>;

generating a plasma in ~~[[said]]~~ the airtight processing chamber for etching ~~[[said]]~~ the organic etching target film~~[[,]]<sub>1</sub>~~ and

etching ~~an organic film containing Si formed on the SiO<sub>2</sub>~~ the organic etching target film ~~to the point until the [[SiO<sub>2</sub>]] protective film is exposed,~~

wherein a resist layer is used as a mask on ~~[[said]]~~ the organic etching target film<sub>1</sub> ~~[[and]]~~

wherein the etching process ceases once the ~~[[SiO<sub>2</sub>]]~~ protective film is exposed, and

wherein the processing gas has a selection ratio greater than approximately 2.0, the selection ratio defined by an etching rate of the organic etching target film divided by an etching rate of the resist layer.

2. (Currently amended) ~~[[An]]~~ The etching method according to claim 1, wherein ~~[[said]]~~ the organic etching target film ~~containing Si~~ is constituted of SiO<sub>2</sub> containing C and H.

3. (Currently amended) ~~[[An]]~~ The etching method according to claim 1, wherein ~~[[the]]~~ a dielectric constant of ~~[[said]]~~ the organic etching target film ~~containing Si~~ is equal to or lower than 3.0.

4. (Currently amended) ~~[[An]]~~ The etching method according to claim 1, wherein ~~[[said]]~~ the organic etching target film ~~containing Si~~ is an organic polysiloxane film.

5. (Currently amended) ~~[[An]]~~ The etching method according to claim 1, wherein ~~[[said]]~~ the processing gas further contains Ar.

6-13. (Canceled)

14. (Currently amended) An etching method for etching an organic etching target film ~~formed on an SiO<sub>2</sub> film placed inside an airtight processing chamber~~, the method comprising:

forming the organic etching target film on a protective film placed inside an airtight processing chamber, the organic etching film containing Si;

introducing a processing gas into ~~[[said]]~~ the airtight processing chamber,  
~~wherein said the processing gas contains~~ containing at least CF<sub>4</sub> and N<sub>2</sub>, ~~wherein the~~  
~~flow rate ratio of CF<sub>4</sub> and N<sub>2</sub> in said processing gas is essentially set within a range of~~  
 $1 \leq (\text{N}_2 \text{ flow rate} / \text{CF}_4 \text{ flow rate}) \leq 4$ ;

generating a plasma in ~~[[said]]~~ the airtight processing chamber for etching ~~[[said]]~~  
the organic etching target film~~[[,]]~~<sub>1</sub>; and

etching ~~an organic~~ the organic etching target film ~~containing Si formed on the~~  
SiO<sub>2</sub> film ~~to the point until the~~ ~~[[SiO<sub>2</sub>]]~~ protective film is exposed,

wherein a resist layer is used as a mask on ~~[[said]]~~ the organic etching target  
film<sub>1</sub> ~~[[and]]~~

wherein the etching process ceases once the ~~[[SiO<sub>2</sub>]]~~ protective film is exposed,  
wherein a flow rate ratio of CF<sub>4</sub> and N<sub>2</sub> in the processing gas is set within a range  
of  $1 \leq (\text{N}_2 \text{ flow rate} / \text{CF}_4 \text{ flow rate}) \leq 4$ .

15-17. (Canceled)